

B.TECH.**THEORY EXAMINATION (SEM–VI) 2016-17****VLSI DESIGN****Time : 3 Hours****Max. Marks : 100****Note : Be precise in your answer. In case of numerical problem assume data wherever not provided.****SECTION – A****1. Explain the following:****10 x 2 = 20**

- (a) Why silicon is preferred over germanium? Explain.
- (b) Define LSI, MSI, VLSI, and ULSI on number of transistor basis?
- (c) Define testing?
- (d) Why scaling has a great importance in VLSI circuits?
- (e) What are the three main domain of design?
- (f) Differentiate between static logic circuits and dynamic logic circuits?
- (g) What are needs for low power VLSI chips?
- (h) Classify semiconductor memories
- (i) What is a twin-well process?
- (j) What are the major drawbacks of pass transistor logic?

SECTION – B**2. Attempt any five of the following questions:****5 x 10 = 50**

- (a) Explain the issues involved in BIST testing?
- (b) Describe the stick layout design style for CMOS circuit design?
- (c) Draw a CMOS inverter and explain its transfer characteristics?
- (d) Define transconductance and output conductance of MOS transistor. Also find expression for Transconductance?
- (e) What are FPGAs? Discuss the salient features of FPGAs
- (f) Explain read/write operation of SRAM memory cell.
- (g) With a neat sketch of cross section of n-channel depletion type MOS transistor, explain the operation and draw the V-I characteristics of the device?
- (h) Describe the polysilicon gate self-aligning NMOS fabrication process?

SECTION – C**Attempt any two of the following questions:****2 x 15 = 30**

- 3. What are the different types of faults in logic circuits? How is the logic gates tested for stuck-at-fault?
- 4. Discuss a combined voltage and dimension scaling model. Compare the scaling factors for the following device parameters: Gate area, Gate capacitance, channel resistance, current density and power dissipation for the different scaling models.
- 5. What are the important parameters of good VLSI design? Enlist the various design techniques and explain fully the cell based design technique.